

## Abstract

Semiconductor component comprising a temporary field stopping area, and method for the production thereof

The invention relates to a semiconductor component comprising a buried temporarily n-doped area (9), which is effective only in the event of turn-off from the conducting to the blocking state of the semiconductor component and prevents chopping of the tail current in order thus to improve the turn-off softness. Said temporarily effective area is created by implantation of K centers (10).

(figure 1A)